

Innovative Silicon's Z-RAM Ultra Dense Memory IP Now Backed by 10th Patent

Memory innovator has 41 additional patents pending and 5 U.S. applications allowed

SANTA CLARA, Calif., June 8, 2006—Innovative Silicon Inc. (ISi), the developer of Z-RAM[®] high density memory IP, today announced that it has been awarded its tenth patent on advanced memory technology: U.S. patent 6,982,918. ISi now has been granted nine U.S. and one Taiwan patent, with another five U.S. patent applications allowed¹. The company also announced that it has an additional 41 patents pending worldwide. The company applied for the patents to protect its one transistor, zero capacitor Z-RAM technology that is five times denser than embedded SRAM and approximately twice as dense as embedded DRAM.

“These patents demonstrate our continued leadership in next-generation memory technology,” said Mark-Eric Jones, president and CEO of ISi. “Since our Z-RAM products can cut an SoC or MPU die cost in half, our patents and other IP provide enormous value to the semiconductor industry. We expect our innovation to continue at this rapid rate into the foreseeable future.”

About Innovative Silicon

Innovative Silicon Inc. (ISi) delivers ultra high density memory IP for embedded SoC, MPU, and portable consumer applications. ISi's Z-RAM[®] technology is double the density of embedded DRAM and five times denser than embedded SRAM, making it the world's lowest-cost semiconductor memory solution. For more information, see www.z-ram.com.

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¹ The five additional applications are approved by the U.S. Patent Office and are currently in the printing process. The patent number and issue date have not yet been assigned.